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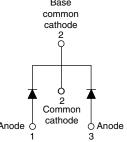
Vishay Semiconductors

Hyperfast Rectifier, 2 x 15 A FRED Pt®



TO-220AB

Diode variation



Common cathode

| Base common cathode 2 | | | | | | | | |
|--------------------------------|-----|------------------------|---------|--|--|--|--|--|
| Anode 0 | Com |) 2 nmon node | Anode 3 | | | | | |

FEATURES

- Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





HALOGEN **FREE**

| TO-220AB |
|--------------------|
| 2 x 15 A |
| 300 V |
| 0.85 V |
| See Recovery table |
| 175 °C |
| |

DESCRIPTION / APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | | |
|-------------------------------------|------------|-----------------------------------|-------------------------|-------------|-------|--|--|--|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | |
| Peak repetitive reverse voltage | | V_{RRM} | | 300 | V | | | | |
| Average rectified forward current | per diode | I _{F(AV)} | T _C = 153 °C | 15 | | | | | |
| | per device | | | 30 | Α | | | | |
| Non-repetitive peak surge current | | I _{FSM} | T _C = 25 °C | 150 | | | | | |
| Operating junction and storage temp | peratures | T _J , T _{Stg} | | -65 to +175 | °C | | | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--|-------------------------------------|--|------|------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | Ι _R = 100 μΑ | 300 | - | - | | |
| Forward voltage | V _F | I _F = 15 A | - | 1.0 | 1.25 | V | |
| | | I _F = 15 A, T _J = 125 °C | - | 0.85 | 0.95 | | |
| | | V _R = V _R rated | - | - | 40 | | |
| Reverse leakage current I _R | | T _J = 125 °C, V _R = V _R rated | - | 8 | 200 | μΑ | |
| Junction capacitance | C _T | V _R = 300 V | - | 38 | - | pF | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8 | - | nH | |



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| DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified) | | | | | | | | |
|---|------------------|--|---|------|------|-------|----|--|
| PARAMETER | SYMBOL | TEST CO | MIN. | TYP. | MAX. | UNITS | | |
| | | $I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | - | 36 | | |
| Payeras rassyony time | t _{rr} | $I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | - | 30 | | |
| Reverse recovery time | | T _J = 25 °C | I _F = 15 A dI _F /dt = 200 A/μs V _R = 200 V | - | 33 | - | ns | |
| | | T _J = 125 °C | | - | 48 | - | | |
| Dook receivery current | I _{RRM} | T _J = 25 °C | | - | 2.8 | - | Α | |
| Peak recovery current | | T _J = 125 °C | | - | 6.5 | - | | |
| Reverse recovery charge | Q _{rr} | T _J = 25 °C | | = | 46 | - | nC | |
| | | T _J = 125 °C | | - | 160 | - | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | |
|--|-----------------------------------|-----------------------------|------|------|-------|--|--|--|
| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNITS | | | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | -65 | = | 175 | °C | | | |
| Thermal resistance, junction to case per diode | R_{thJC} | - | - | 1.4 | °C/W | | | |
| Marking device | | Case style TO-220AB 30CTH03 | | | | | | |

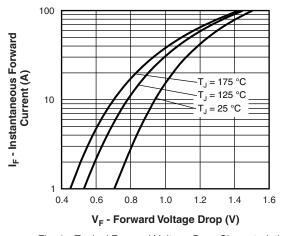


Fig. 1 - Typical Forward Voltage Drop Characteristics

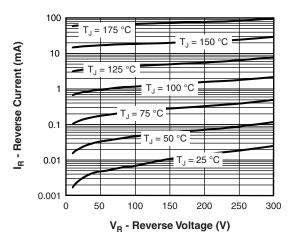


Fig. 2 - Typical Values of Reverse Current vs.
Reverse Voltage

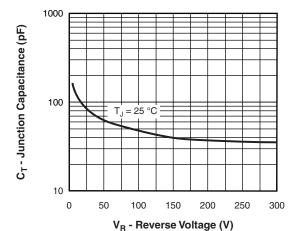


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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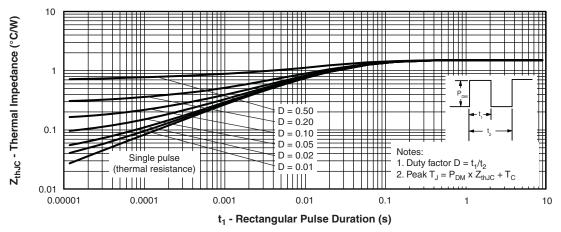


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

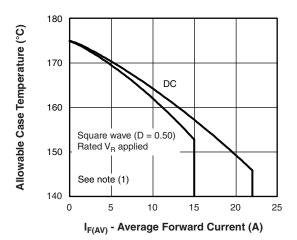


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

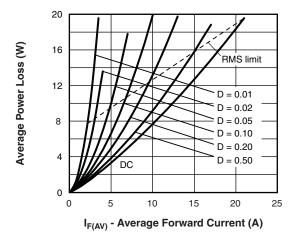


Fig. 6 - Forward Power Loss Characteristics

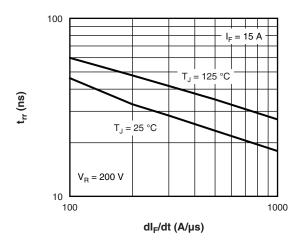


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

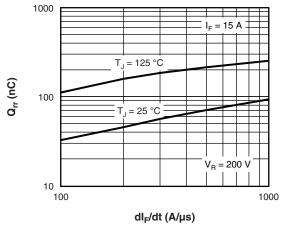


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{th,JC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R

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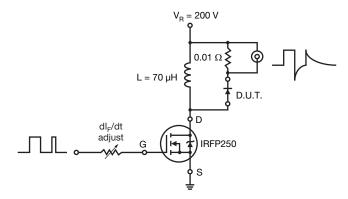
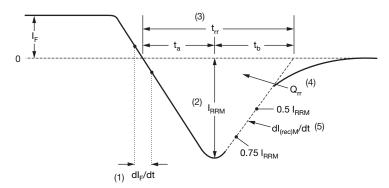


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

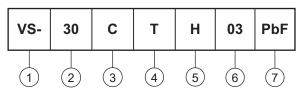
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-30CTH03PbF, VS-30CTH03-N3

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ORDERING INFORMATION TABLE

Device code



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2 - Current rating (30 = 30 A)

Circuit configuration:

C = common cathode

4 - Package:

T = TO-220

5 - H = hyperfast recovery

Voltage rating (03 = 300 V)

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | | | | |
|--------------------------------|------------------|------------------------|-------------------------|--|--|--|--|--|
| PREFERRED P/N | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | | | |
| VS-30CTH03PbF | 50 | 1000 | Antistatic plastic tube | | | | | |
| VS-30CTH03-N3 | 50 | 1000 | Antistatic plastic tube | | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | | |
|----------------------------|-------------|--------------------------|--|--|--|--|
| Dimensions | TO-220AB | www.vishay.com/doc?95222 | | | | |
| Dort marking information | TO-220ABPbF | www.vishay.com/doc?95225 | | | | |
| Part marking information | TO-220AB-N3 | www.vishay.com/doc?95028 | | | | |



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

| SYMBOL | MILLIN | IETERS | INC | HES | NOTES |
|--------|--------|--------|-------|-------|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| Α | 4.25 | 4.65 | 0.167 | 0.183 | |
| A1 | 1.14 | 1.40 | 0.045 | 0.055 | |
| A2 | 2.56 | 2.92 | 0.101 | 0.115 | |
| b | 0.69 | 1.01 | 0.027 | 0.040 | |
| b1 | 0.38 | 0.97 | 0.015 | 0.038 | 4 |
| b2 | 1.20 | 1.73 | 0.047 | 0.068 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 |
| С | 0.36 | 0.61 | 0.014 | 0.024 | |
| c1 | 0.36 | 0.56 | 0.014 | 0.022 | 4 |
| D | 14.85 | 15.25 | 0.585 | 0.600 | 3 |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 | |
| D2 | 11.68 | 12.88 | 0.460 | 0.507 | 6 |

| SYMBOL | MILLIM | IETERS | INC | HES | NOTES |
|---------|------------|--------|------------|-------|-------|
| STIMBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| E | 10.11 | 10.51 | 0.398 | 0.414 | 3, 6 |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 | 6 |
| E2 | - | 0.76 | - | 0.030 | 7 |
| е | 2.41 | 2.67 | 0.095 | 0.105 | |
| e1 | 4.88 | 5.28 | 0.192 | 0.208 | |
| H1 | 6.09 | 6.48 | 0.240 | 0.255 | 6, 7 |
| L | 13.52 | 14.02 | 0.532 | 0.552 | |
| L1 | 3.32 | 3.82 | 0.131 | 0.150 | 2 |
| ØΡ | 3.54 | 3.73 | 0.139 | 0.147 | |
| Q | 2.60 | 3.00 | 0.102 | 0.118 | |
| θ | 90° to 93° | | 90° to 93° | | |
| | | • | • | • | |

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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